	Туре	L·#	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	935	257/786.ccls. and @ay<1999	USPAT; EPO; JPO; DERWEN T; IBM_TI	2002/08/12 06:54
2	BRS	L2	272	loc and memory and array and pad	USPAT; EPO; JPO; DERWEN T; IBM_TD	2002/08/12 06:55
3	BRS	L3	0	(algan gaaln) and clad and (quantum adj well) and @ay<1995	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 07:37
4	BRS	L4	416	gan and ((laser) (light adj emitting adj diode)) and @ay<1995	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/08/12 07:38
5	BRS	L5	40	and (quantum adj well)	r; IBM_TD	2002/08/12 07:39

East Search 8/7/02 Search L No. Hits Text Search Data Bases (light adj emitting adj (diode device)) and ((ingan gainn) near5 (mqw ((multi USPAT; EPO; JPO; BRS LI 94 multiple) adj quantum adj well))) 8/7/02 15:05 Derwent; IBM TDB USPAT; EPO; JPO; BRS L2 1 and second adj clad\$4 8/7/02 15:06 Derwent; IBM TDB USPAT; EPO; JPO; ((ingan gainn) near5 (mqw ((multi BRS L5 141 multiple) adj quantum adj well))) 8/7/02 15:48 Derwent; IBM TDB USPAT; EPO; JPO; BRS L6 5 and second adj clad\$4 26 8/7/02 15:06 Derwent; IBM TDB ((gan) near5 (mqw ((multi multiple) adj USPAT; EPO; JPO; BRS L7 129 quantum adj well))) 8/7/02 15:48 Derwent; IBM TDB

Search Result

USPAT	Date	Page	Title 4	Cl/Sub	Cl/Sub	Inventor
US 5777350 A	19980707		Nitride semiconductor light-emitting device	257/96	257/103; 257/13; 257/76; 257/97; 372/45	Nakamura, Shuji et al.
US \$470045 A	10071001		Integrated heterostructures of Group III- V nitride semiconductor materials including epitaxial ohmic contact, non- nitride buffer layer and methods of			reactive at the state of the st
US 5679965 A	19971021	49	fabricating same	257/103	257/104	Schetzina, Jan Frederick
			Integrated heterostructures of Group III- V nitride semiconductor materials including epitaxial ohmic contact non- nitride buffer layer and methods of		257/101; 257/198;	
US 5670798 A	19970923		fabricating same	257/96	257/458; 257/76	Schetzina, Jan Frederick

Search	L No.	Hits	Text Search		2/18/
Scarch	L ING.	11165	Text Search		Data Bases
	ľ	i	((((light adj emitting adj (diode device)))		
	1				
BRS		205	and (quantum adj well) and (gan ingan		USPAT; EPO; JPO;
DK3		205	algan gainn gaaln)) and barrier	2/18/02 11:32	Derwent; IBM TDB
		ı	((((light adj emitting adj (diode device)))		
			and (quantum adj well) and (gan ingan		
	1	İ	algan gainn gaaln)) and @ay<1995) and		USPAT; EPO; JPO;
BRS		11	barrier	2/17/02 21:15	Derwent; IBM TDB
	ļ		("257/81,84,88,92,93,98,99,100,690,698		USPAT; EPO; JPO;
IS&R	L15	6180	,700").CCLS.	2/18/02 11:46	
			15 and (mqw (multi\$4 adj quantum adj		USPAT; EPO; JPO;
BRS	L16	107	(well))	2/18/02 11:48	
				2,10,02 11.10	USPAT; EPO; JPO;
BRS	L17	29	16 and (gan algan ingan gaaln gainn)	2/18/02 11:52	
			(Same Para angua Buma)	2/18/02 11.32	
BRS	L18	2	17 and @ay<1995	2/19/02 11 52	USPAT; EPO; JPO;
	- 2.0	<del></del>	17 and (19ay -1995)	2/18/02 11:52	Derwent; IBM TDB
	İ		(((light adi amitting adi (dia ta davian)))		
BRS	1 122	1265	(((light adj emitting adj (diode device)))		USPAT; EPO; JPO;
DI/O	L23	1365	and (gan ingan algan gainn gaaln))	2/18/02 12:21	Derwent; IBM TDB
DDC					USPAT; EPO; JPO;
BRS	L24	236	23 and @ay<1995	2/18/02 12:22	Derwent; IBM TDB

Search Result USPAT	Date	D X	Is a real section of	J 2	W. 1777 - 2007 - 2007 - 2007	
USIAI	Date	Page	THE	Cl/Sub	Cl/Sub	Inventor
			GALLIUM NITRIDE COMPOUND			
ID 07162020 A	10050602	_	SEMICONDUCTOR LIGHT			NAKAMURA, SHUJI ,
JP 07162038 A	19950623	5	EMITTING DIODE			IWASA, SHIGETO
ID 2000261027	2000000		SEMICONDUCTOR LIGHT			
JP 2000261037 A			EMITTING DEVICE			KANEIWA, SHINJI
US 4862471 A	19890829	4	Semiconductor light emitting device	372/45	257/191 ; 257/22	Pankove, Jacques I.
			Electroluminescent device of compound	İ	257/101 ; 257/103 ;	
US 5237182 A	19930817	13	semiconductor with buffer layer	257/15	257/94 : 257/96	Kitagawa, Masahiko, et al
			Blue light-emitting diode with degenerate		257/101; 257/102;	Kitagawa, Wasaniko , et al
US 5338944 A	19940816	9	junction structure	257/76	257/103 ; 257/77	Edmond, John A., et al.
			Compound semicondutor light-emitting	251170	2311103,231111	Editiona, John A., et al.
US 5432808 A	19950711	16		372/45	257/77 ; 372/44	Hatano, Ako, et al.
US 5537433 A	19960716	21	Semiconductor light emitter	372/45	257/98 ; 372/43	Watanabe, Masanori
				0.2,10	257/103 ; 257/22 ;	watanabe, wasanon
}					257/615 ; 257/741 ;	
					257/745; 257/750;	
					257/751; 257/76;	
					257/763 ; 257/764 ;	
			Gallium nitride-based III-V group		257/765 ; 257/766 ;	
	}		compound semiconductor device and		257/770; 257/771;	
US 5563422 A	19961008	23		257/13	257/79	Nakamura, Shuji, et al.
			Light-emitting gallium nitride-based	20 // 10	257/101 ; 257/201 ;	ivakaniara, Shaji , et al.
US 5578839 A	19961126			257/96	257/613	Nakamura, Shuji, et al.
			High brightness electroluminescent		257/103 ; 257/627 ;	
į			device, emitting in the green to		257/94 ; 372/43 ;	
			ultraviolet spectrum, and method of		372/45 : 438/32 :	
JS 5585648 A	19961217		I	257/77		Tischler, Michael A.